



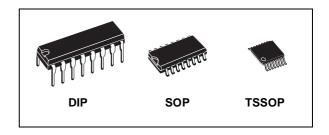
3 TO 8 LINE DECODER

- HIGH SPEED:
 - t_{PD} = 15ns (TYP.) at V_{CC} = 6V
- LOW POWER DISSIPATION: $I_{CC} = 4\mu A(MAX.)$ at $T_A=25$ °C
- HIGH NOISE IMMUNITY: V_{NIH} = V_{NIL} = 28 % V_{CC} (MIN.)
- SYMMETRICAL OUTPUT IMPEDANCE: |I_{OH}| = I_{OL} = 4mA (MIN)
- BALANCED PROPAGATION DELAYS: t_{PLH} ≅ t_{PHL}
- WIDE OPERATING VOLTAGE RANGE: V_{CC} (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 238



The M74HC238 is an high speed CMOS 3 TO 8 LINE DECODER fabricated with silicon gate C^2MOS technology.

If the device is enabled, 3 binary select inputs (A, B and C) determine which one of outputs will go high. When enable input G1 is held "Low" or either G2A or G2B is held "High" decoding function is



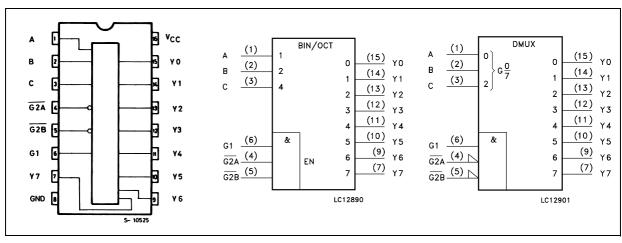
ORDER CODES

PACKAGE	TUBE	T & R
DIP	M74HC238B1R	
SOP	M74HC238M1R	M74HC238RM13TR
TSSOP		M74HC238TTR

inhibited and all the 8 outputs go low. Three enable inputs are provided to ease cascade connection and application of this address decoder in memory systems.

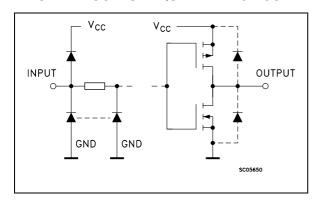
All inputs are equipped with protection circuits against static discharge and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



July 2001 1/10

INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

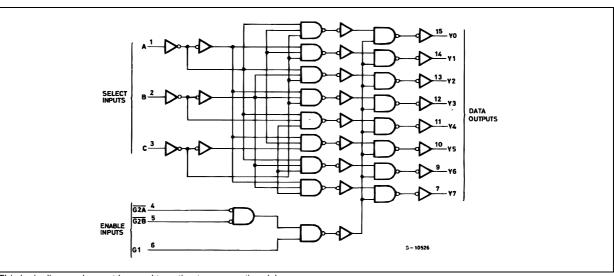
PIN No	SYMBOL	NAME AND FUNCTION
1, 2, 3	A, B, C	Data Inputs
4, 5	G2A G2B	Enable Input (Active LOW)
6	G1	Data Enable Input (Active HIGH)
15, 14, 13, 12, 11, 10, 9, 7	Y0 to Y7	Outputs
8	GND	Ground (0V)
16	V _{CC}	Positive Supply Voltage

TRUTH TABLE

		INP	UTS			OUTPUTS								
E	ENABLI	E		SELEC.	Т				0011	7013				SELECTED OUTPUT
G2B	G2A	G1	С	В	Α	Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y7	
Х	Χ	L	Х	Х	Х	L	L	L	L	L	L	L	L	NONE
Х	Н	Χ	Х	Х	Х	L	L	L	L	L	L	L	L	NONE
Н	Х	Χ	Х	Х	Х	L	L	L	L	L	L	L	L	NONE
L	L	Н	L	L	L	Н	L	L	L	L	L	L	L	Y0
L	L	Н	L	L	Н	L	Н	L	L	L	L	L	L	Y1
L	L	Н	L	Н	L	L	L	Н	L	L	L	L	L	Y2
L	L	Н	L	Н	Н	L	L	L	Н	L	L	L	L	Y3
L	L	Н	Н	L	L	L	L	L	L	Н	L	L	L	Y4
L	L	Н	Н	L	Н	Ĺ	L	L	L	L	Н	L	L	Y5
L	L	Н	Н	Н	L	L	L	L	L	L	L	Н	L	Y6
L	L	Н	Н	Н	Н	L	L	L	L	L	L	L	Н	Y7

X : Don't Care

LOGIC DIAGRAM



This logic diagram has not be used to estimate propagation delays

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7	V
VI	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
Ιο	DC Output Current	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
P_{D}	Power Dissipation	500(*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

(*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Value	Unit
V _{CC}	Supply Voltage		2 to 6	V
VI	Input Voltage		0 to V _{CC}	V
Vo	Output Voltage		0 to V _{CC}	V
T _{op}	Operating Temperature		-55 to 125	°C
	Input Rise and Fall Time	V _{CC} = 2.0V	0 to 1000	ns
t _r , t _f		V _{CC} = 4.5V	0 to 500	ns
		V _{CC} = 6.0V	0 to 400	ns

DC SPECIFICATIONS

		To	est Conditions				Value				
Symbol	Parameter	v _{cc}		T _A = 25°C			-40 to 85°C		-55 to 125°C		Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V _{IH}	High Level Input	2.0		1.5			1.5		1.5		
	Voltage	4.5		3.15			3.15		3.15		V
		6.0		4.2			4.2		4.2		
V_{IL}	Low Level Input	2.0				0.5		0.5		0.5	
	Voltage	4.5				1.35		1.35		1.35	V
		6.0				1.8		1.8		1.8	
V _{OH}	V _{OH} High Level Output		I _O =-20 μA	1.9	2.0		1.9		1.9		
	Voltage	4.5	I _O =-20 μA	4.4	4.5		4.4		4.4		
		6.0	I _O =-20 μA	5.9	6.0		5.9		5.9		V
		4.5	I _O =-4.0 mA	4.18	4.31		4.13		4.10		
		6.0	I _O =-5.2 mA	5.68	5.8		5.63		5.60		
V _{OL}	Low Level Output	2.0	I _O =20 μA		0.0	0.1		0.1		0.1	
	Voltage	4.5	I _O =20 μA		0.0	0.1		0.1		0.1	
		6.0	I _O =20 μA		0.0	0.1		0.1		0.1	V
		4.5	I _O =4.0 mA		0.17	0.26		0.33		0.40	
		6.0	I _O =5.2 mA		0.18	0.26		0.33		0.40	
I _I	Input Leakage Current	6.0	$V_I = V_{CC}$ or GND			± 0.1		± 1		± 1	μΑ
I _{CC}	Quiescent Supply Current	6.0	$V_I = V_{CC}$ or GND			4		40		80	μА

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ns}$)

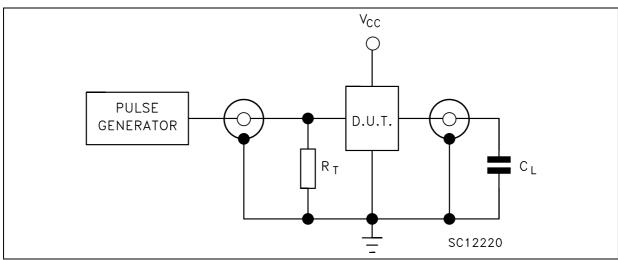
		Te	est Conditions	Value								
Symbol	Symbol Parameter			T _A = 25°C			-40 to 85°C		-55 to 125°C		Unit	
		V _{CC} (V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.			
t _{TLH} t _{THL}	Output Transition	2.0			30	75		95		110		
	Time	4.5			8	15		19		22	ns	
		6.0			7	13		16		19		
t _{PLH} t _{PHL}	Propagation Delay	2.0			50	150		190		225		
	Time (A, B, C - Y)	4.5			17	30		38		45	ns	
		6.0			15	26		32		38		
t _{PLH} t _{PHL}	Propagation Delay	2.0			50	150		190		225		
	Time (G1 - Y)	4.5			17	30		38		45	ns	
		6.0			15	26		32		38		
t _{PLH} t _{PHL}	Propagation Delay Time (G2 - Y)	2.0			50	150		190		225		
		4.5			17	30		38		45	ns	
		6.0			15	26		32		38		

CAPACITIVE CHARACTERISTICS

		Test Conditions		Value								
Symbol	Parameter	V _{CC} (V)	V _{CC}	V _{CC}	T _A = 25°C			-40 to 85°C		-55 to 125°C		Unit
			Min.	Тур.	Max.	Min.	Max.	Min.	Max.			
C _{IN}	Input Capacitance	5.0			5	10		10		10	pF	
C _{PD}	Power Dissipation Capacitance (note 1)	5.0			53						pF	

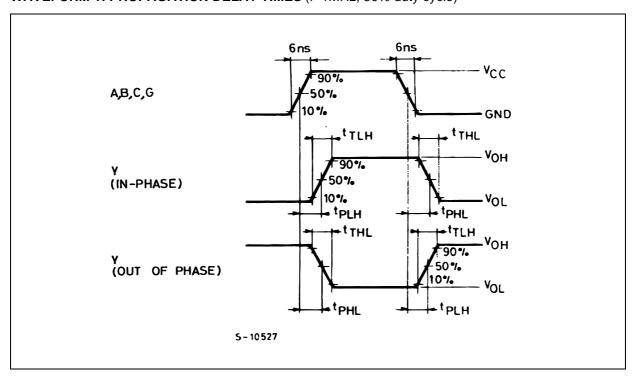
¹⁾ C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}$

TEST CIRCUIT



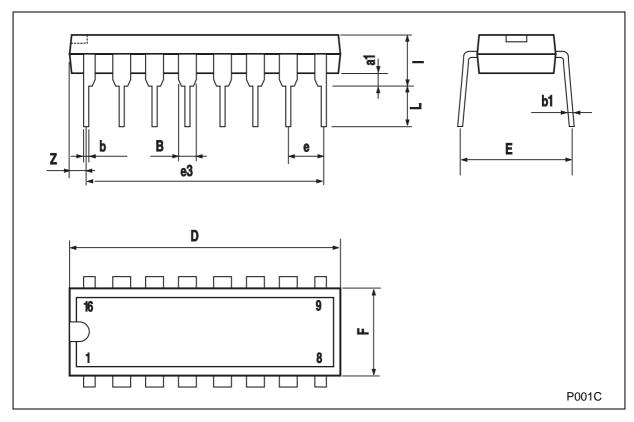
 C_L = 50pF or equivalent (includes jig and probe capacitance) R_T = Z_{OUT} of pulse generator (typically 50Ω)

WAVEFORM 1: PROPAGATION DELAY TIMES (f=1MHz; 50% duty cycle)



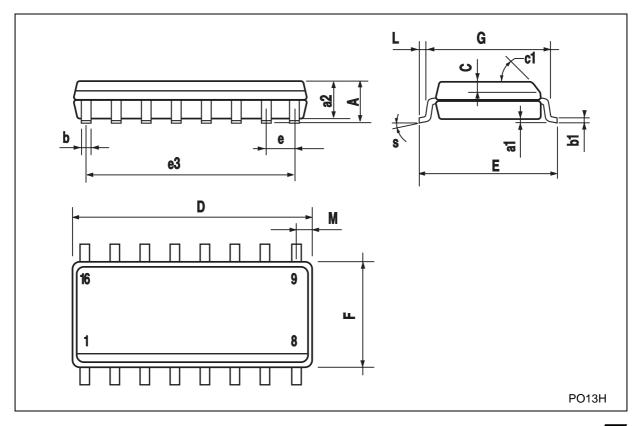
Plastic DIP-16 (0.25) MECHANICAL DATA

DIM		mm.		inch					
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.			
a1	0.51			0.020					
В	0.77		1.65	0.030		0.065			
b		0.5			0.020				
b1		0.25			0.010				
D			20			0.787			
E		8.5			0.335				
е		2.54			0.100				
e3		17.78			0.700				
F			7.1			0.280			
I			5.1			0.201			
L		3.3			0.130				
Z			1.27			0.050			



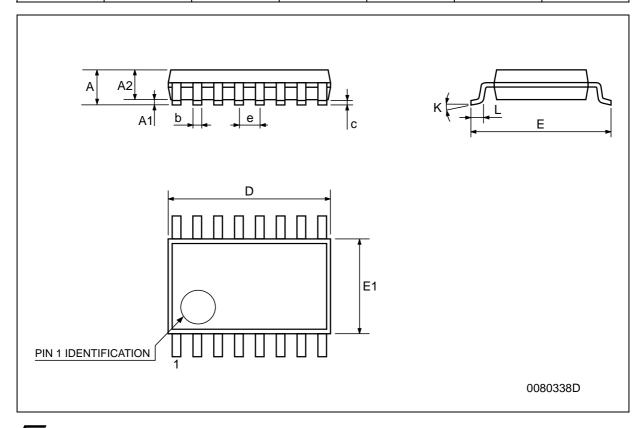
SO-16 MECHANICAL DATA

DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
С		0.5			0.019	
c1			45°	(typ.)	•	•
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
е		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
М			0.62			0.024
S			8° (max.)	•	



TSSOP16 MECHANICAL DATA

DIM		mm.		inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
А			1.2			0.047		
A1	0.05		0.15	0.002	0.004	0.006		
A2	0.8	1	1.05	0.031	0.039	0.041		
b	0.19		0.30	0.007		0.012		
С	0.09		0.20	0.004		0.0089		
D	4.9	5	5.1	0.193	0.197	0.201		
E	6.2	6.4	6.6	0.244	0.252	0.260		
E1	4.3	4.4	4.48	0.169	0.173	0.176		
е		0.65 BSC			0.0256 BSC			
К	0°		8°	0°		8°		
L	0.45	0.60	0.75	0.018	0.024	0.030		



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